

FEATURES

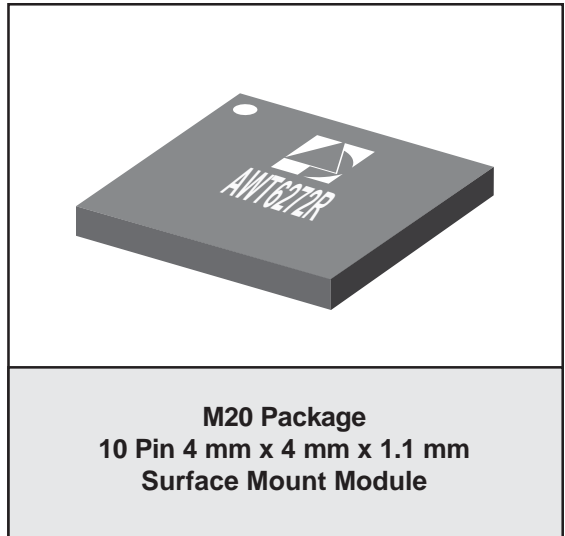
- InGaP HBT Technology
- High Efficiency:
 - 44 % @ P_{OUT} = +29 dBm
 - 20 % @ P_{OUT} = +16 dBm
 - 15 % @ P_{OUT} = +7 dBm
- Low Quiescent Current: 16 mA
- Low Leakage Current in Shutdown Mode: <1 μA
- V_{REF} = +2.85 V (+2.75 V min over temp)
- Optimized for a 50 Ω System
- Low Profile Miniature Surface Mount Package
Option: 1.1 mm Max
- RoHS Compliant Package, 250 °C MSL-3
- HSDPA Compliant (no backoff)

APPLICATIONS

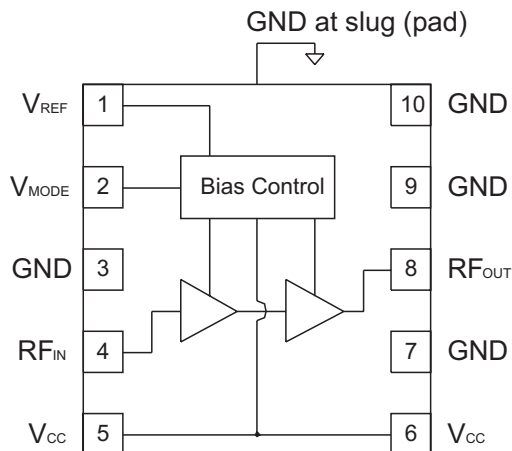
- Dual Band WCDMA Wireless Handsets
- Dual Mode 3GPP Wireless Handsets

PRODUCT DESCRIPTION

The AWT6272R meets the increasing demands for higher output power in UMTS handsets. The PA module is optimized for V_{REF} = +2.85 V, a requirement for compatibility with the Qualcomm® 6250 chipset. The device is manufactured on an advanced InGaP HBT



MMIC technology offering state-of-the-art reliability, temperature stability, and ruggedness. Selectable bias modes that optimize efficiency for different output power levels, and a shutdown mode with low leakage current, increase handset talk and standby time. The self-contained 4 mm x 4 mm x 1.1 mm surface mount package incorporates matching networks optimized for output power, efficiency, and linearity in a 50 Ω system.


Figure 1: Block Diagram

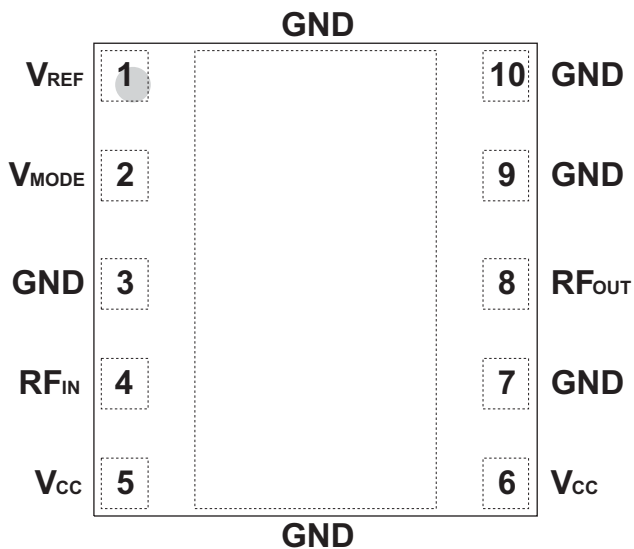


Figure 2: Pinout (X-ray Top View)

Table 1: Pin Description

| PIN | NAME | DESCRIPTION |
|-----|------------|-------------------|
| 1 | V_{REF} | Reference Voltage |
| 2 | V_{MODE} | Mode Control |
| 3 | GND | Ground |
| 4 | RF_{IN} | RF Input |
| 5 | V_{CC} | Supply Voltage |
| 6 | V_{CC} | Supply Voltage |
| 7 | GND | Ground |
| 8 | RF_{OUT} | RF Output |
| 9 | GND | Ground |
| 10 | GND | Ground |

ELECTRICAL CHARACTERISTICS

Table 2: Absolute Minimum and Maximum Ratings

| PARAMETER | MIN | MAX | UNIT |
|-------------------------------------|-----|------|------|
| Supply Voltage (V_{CC}) | 0 | +5 | V |
| Mode Control Voltage (V_{MODE}) | 0 | +3.5 | V |
| Reference Voltage (V_{REF}) | 0 | +3.5 | V |
| RF Input Power (P_{IN}) | - | +10 | dBm |
| Storage Temperature (T_{STG}) | -40 | +150 | °C |

Stresses in excess of the absolute ratings may cause permanent damage. Functional operation is not implied under these conditions. Exposure to absolute ratings for extended periods of time may adversely affect reliability.

Table 3: Operating Ranges

| PARAMETER | MIN | TYP | MAX | UNIT | COMMENTS |
|---|--|----------------------------------|---------------------|------|---|
| Operating Frequency (f) | 824 | - | 849 | MHz | |
| Supply Voltage (V_{CC}) | +3.2 - | +3.4 +1.5 | +4.2 - | V | $P_{OUT} \leq +29$ dBm $P_{OUT} \leq 7$ dBm |
| Reference Voltage (V_{REF}) | +2.75 0 | +2.85 - | +2.95 +0.5 | V | PA "on" PA "shut down" |
| Mode Control Voltage (V_{MODE}) | +2.5 0 | +2.8 - | +3.1 +0.5 | V | Low Bias Mode High Bias Mode |
| RF Output Power (P_{OUT}) 3GPP HSDPA Case A HSDPA Case B HSDPA Case C | +28.5 ⁽¹⁾ +27.5 ⁽¹⁾ +26.5 ⁽¹⁾ +26.0 ⁽¹⁾ | +29.0 +28.0 +27.0 +26.5 | - - - - | dBm | $1/15 \leq \beta_c/\beta_d \leq 12/15$ $13/15 \leq \beta_c/\beta_d \leq 15/8$ $15/7 \leq \beta_c/\beta_d \leq 15/0$ |
| Case Temperature (T_C) | -20 | - | +110 ⁽²⁾ | °C | |

The device may be operated safely over these conditions; however, parametric performance is guaranteed only over the conditions defined in the electrical specifications.

Notes:

(1) For operation at $V_{CC} = +3.2$ V, P_{OUT} is derated by 0.5 dB.

(2) For operation at 110 °C (T_C), P_{OUT} is derated by 1.0 dB.

Table 4: Electrical Specifications
 (T_C = +25 °C, V_{CC} = +3.4 V, V_{REF} = +2.85 V, 50 Ω system)

| PARAMETER | MIN | TYP | MAX | UNIT | COMMENTS |
|--|------------------|-------------------|-------------------|--------|--|
| Gain | 24.5 14 13 | 26.5 16 15 | 29 18 17 | dB | P _{OUT} = +29 dBm, V _{MODE} = 0 V P _{OUT} = +16 dBm, V _{MODE} = +2.85 V P _{OUT} = +7 dBm, V _{CC} = 1.5 V, V _{MODE} = +2.85 V |
| ACLR1 at 5 MHz offset ⁽¹⁾ | - - - | -40 -45 -45 | -38 -38 -38 | dBc | P _{OUT} = +29 dBm, V _{MODE} = 0 V P _{OUT} = +16 dBm, V _{MODE} = +2.85 V P _{OUT} = +7 dBm, V _{CC} = 1.5 V, V _{MODE} = +2.85 V |
| ACLR2 at 10 MHz offset | - - - | -56 -56 -58 | -48 -48 -48 | dBc | P _{OUT} = +29 dBm, V _{MODE} = 0 V P _{OUT} = +16 dBm, V _{MODE} = +2.85 V P _{OUT} = +7 dBm, V _{CC} = 1.5 V, V _{MODE} = +2.85 V |
| Power-Added Efficiency ⁽¹⁾ | 41 17 12 | 44 20 14.5 | - - - | % | P _{OUT} = +29 dBm, V _{MODE} = 0 V P _{OUT} = +16 dBm, V _{MODE} = +2.85 V P _{OUT} = +7 dBm, V _{CC} = 1.5 V, V _{MODE} = +2.85 V |
| Quiescent Current (I _q) | - | 16 | 22 | mA | V _{MODE} = +2.85 V, V _{CC} = 3.4 V |
| Reference Current | - | 4 | 5 | mA | through V _{REF} pin |
| Mode Control Current | - | 0.6 | 1 | mA | through V _{MODE} pin, V _{MODE} = +2.85 V |
| Leakage Current | - | <1 | 5 | μA | V _{CC} = +4.2 V, V _{REF} = 0 V, V _{MODE} = 0 V |
| Noise in Receive Band | - - | -134 -142 | -133 -140 | dBm/Hz | 869 MHz to 894 MHz P _{OUT} = +28.5 dBm, V _{MODE} = 0 V 869 MHz to 894 MHz P _{OUT} = +16 dBm, V _{MODE} = +2.85 V |
| Harmonics 2fo 3fo, 4fo | - - | -45 -50 | -30 -30 | dBc | |
| Input Impedance | - | - | 2:1 | VSWR | |
| Spurious Output Level (all spurious outputs) | - | - | -70 | dBc | P _{OUT} ≤ +29 dBm In-band load VSWR < 5:1 Out-of-band load VSWR < 10:1 Applies over all operating conditions |
| Load mismatch stress with no permanent degradation or failure | 10:1 | - | - | VSWR | Applies over full operating range |

Notes:

(1) ACLR and Efficiency measured at 836.5 MHz.

APPLICATION INFORMATION

To ensure proper performance, refer to all related Application Notes on the ANADIGICS web site: <http://www.anadigics.com>

Shutdown Mode

The power amplifier may be placed in a shutdown mode by applying logic low levels (see Operating Ranges table) to both the V_{REF} and V_{MODE} voltages.

Bias Modes

The power amplifier may be placed in either a Low Bias mode or a High Bias mode by applying the

appropriate logic level (see Operating Ranges table) to the V_{MODE} voltage. The Bias Control table lists the recommended modes of operation for various applications.

Three operating modes are recommended to optimize current consumption. High Bias/High V_{CC} operating mode is for P_{OUT} levels ≥ 16 dBm. At ~ 16 dBm - 7 dBm, the PA should be "Mode Switched" to Low Bias Mode. For P_{OUT} levels $\leq \sim 7$ dBm, the V_{CC} can be switched to 1.5 V (Low Bias Mode is also used for this P_{OUT} range).

Table 5: Bias Control

| APPLICATION | P_{OUT} LEVELS | BIAS MODE | V_{REF} | V_{MODE} | V_{CC} |
|-------------------|-------------------------------|-----------|-----------|------------|----------|
| CDMA - low power | $\leq +7$ dBm | Low | +2.85 V | +2.85 V | +1.5 |
| CDMA - med power | $7 \leq P_{OUT} \leq +16$ dBm | Low | +2.85 V | +2.85 V | +3.4 |
| CDMA - high power | $> +16$ dBm | High | +2.85 V | 0 V | +3.4 |
| Shutdown | - | Shutdown | 0 V | 0 V | - |

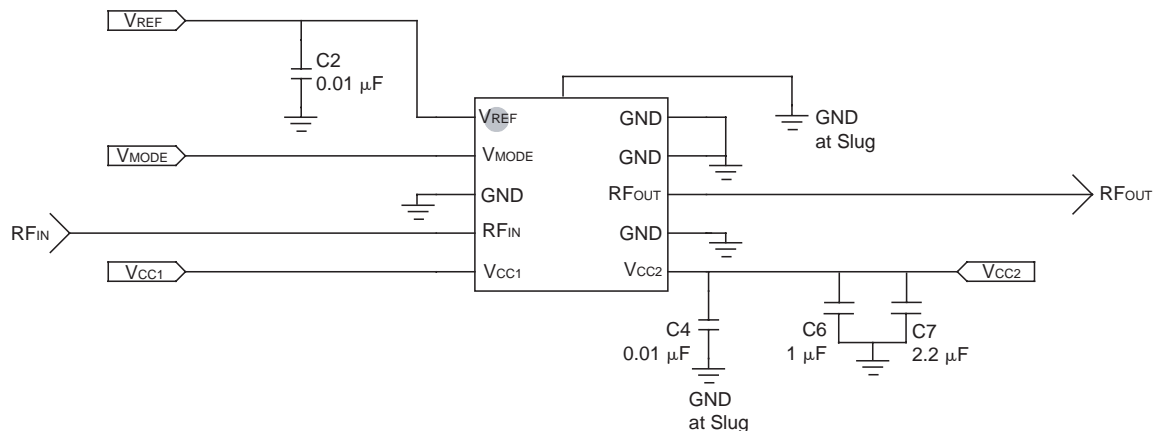
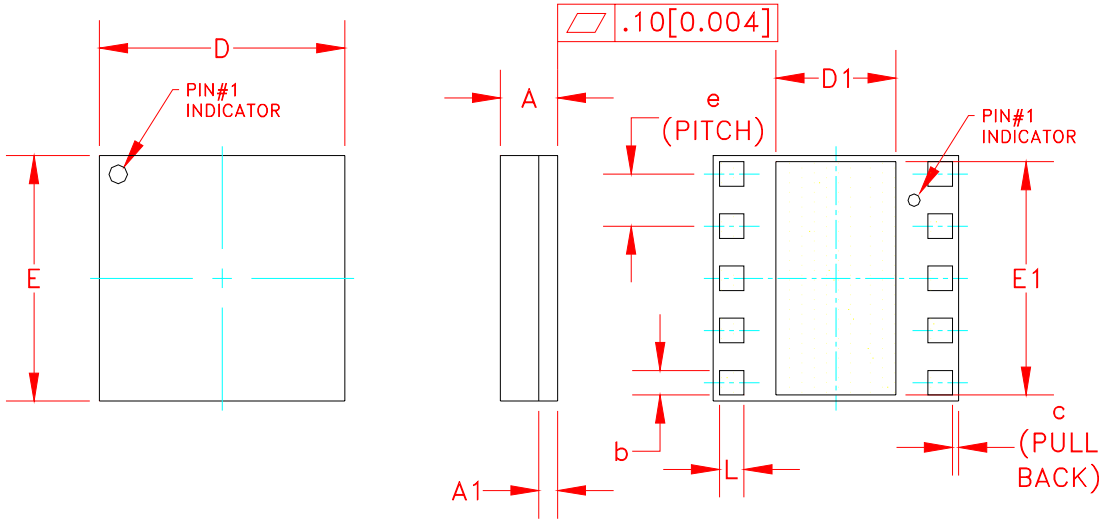


Figure 3: Application Schematic

PACKAGE OUTLINE



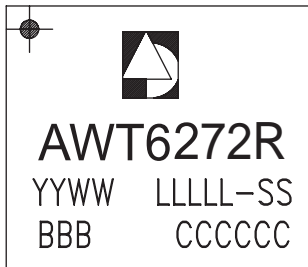
| S _{YMBOL} | MILLIMETERS | | | INCHES | | | NOTE |
|--------------------|-------------|------|------|--------|-------|-------|------|
| | MIN. | NOM. | MAX. | MIN. | NOM. | MAX. | |
| A | 0.90 | 1.00 | 1.10 | 0.035 | 0.039 | 0.043 | - |
| A1 | - | 0.35 | - | - | 0.014 | - | - |
| b | 0.35 | - | 0.60 | 0.013 | - | 0.024 | 3 |
| c | - | 0.10 | - | - | 0.004 | - | - |
| D | 3.88 | 4.00 | 4.12 | 0.152 | 0.157 | 0.162 | - |
| D1 | 1.90 | - | 2.20 | 0.075 | - | 0.086 | - |
| E | 3.88 | 4.00 | 4.12 | 0.152 | 0.157 | 0.162 | - |
| E1 | 3.75 | - | 3.85 | 0.148 | - | 0.152 | - |
| e | - | 0.85 | - | - | 0.033 | - | 3 |
| L | 0.35 | - | 0.60 | 0.013 | - | 0.024 | 3 |

NOTES:

1. CONTROLLING DIMENSIONS: MILLIMETERS
2. UNLESS SPECIFIED TOLERANCE=±0.076[0.003].
3. PADS (INCLUDING CENTER) SHOWN UNIFORM SIZE FOR REFERENCE ONLY. ACTUAL PAD SIZE AND LOCATION WILL VARY WITHIN MIN. AND MAX. DIMENSIONS ACCORDING TO SPECIFIC LAMINATE DESIGN.

Figure 4: M20 Package Outline - 10 Pin 4 mm x 4 mm x 1.1 mm Surface Mount Module

TOP BRAND

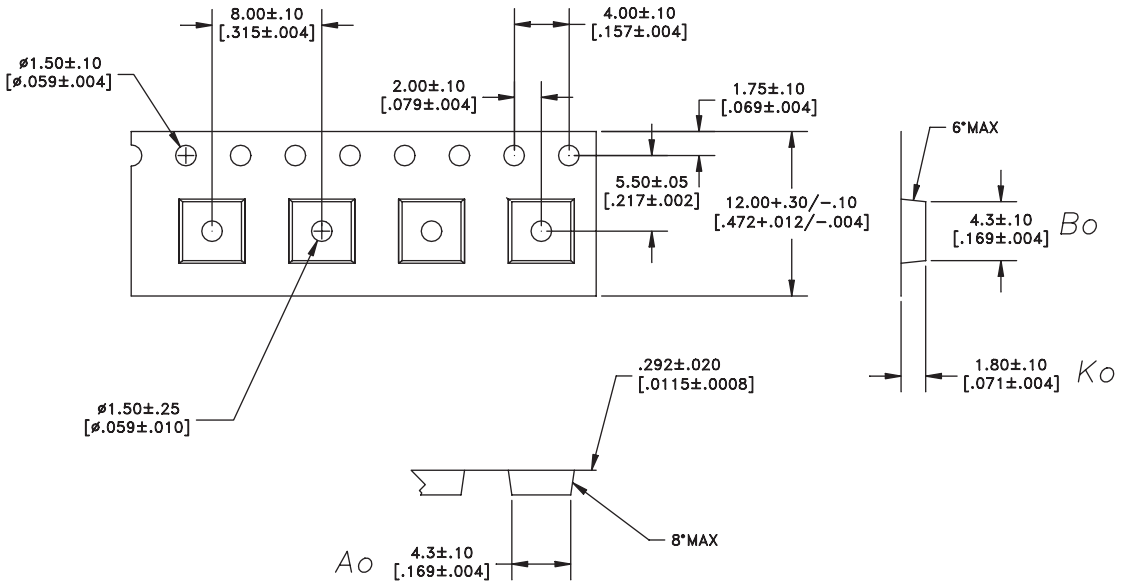


NOTES:

1. ANADIGICS LOGO SIZE: X=0.040±0.010 Y=0.048±0.010
2. PART # AWT6272R
3. YEAR AND WORK WEEK: YYWW: YY = YEAR, WW = WORK WEEK
4. LOT - WAFER I.D.: LLLLL - SS = WAFER/LOT I.D.
5. PIN 1 INDICATOR: MOLD NOTCH -or- INK DOT
6. BOM # BBB
7. COUNTRY CODE: CCCCC
8. TYPE : ELITE
SIZE : AS LARGE AS POSSIBLE
LASER MARKED

Figure 5: Branding Specification

COMPONENT PACKAGING



DIMENSIONS ARE IN MILLIMETERS [INCHES]
STANDARD TOLERANCES

Figure 6: Tape & Reel Packaging

Table 6: Tape & Reel Dimensions

| PACKAGE TYPE | TAPE WIDTH | POCKET PITCH | REEL CAPACITY | MAX REEL DIA |
|----------------------|------------|--------------|---------------|--------------|
| 4 mm x 4 mm x 1.1 mm | 12 mm | 8 mm | 2500 | 13" |

ORDERING INFORMATION

| ORDER NUMBER | TEMPERATURE RANGE | PACKAGE DESCRIPTION | COMPONENT PACKAGING |
|---------------------|--------------------------|---|-------------------------------------|
| AWT6272RM20P8 | -20 °C to +110 °C | RoHS Compliant 10 Pin 4 mm x 4 mm x 1.1 mm Surface Mount Module | Tape and Reel, 2500 pieces per Reel |



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